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25 LE

NC - No internal connection

		SCEST27C-TEBROF	
•	Member of the Texas Instruments <i>Widebus</i> ™ Family		R DL PACKAGE P VIEW)
•	<i>EPIC</i> <sup>™</sup> (Enhanced-Performance Implanted CMOS) Submicron Process	OE [ 1 Y1 ] 2	48 CLK 47 A1
•	Ideal for Use in PC100 Register DIMM	Y2 3	46 A2
٠	Output Ports Have Equivalent 26- $\Omega$ Series	GND 4	45 GND
	Resistors, So No External Resistors Are	Y3 🛛 5	44 🛛 A3
	Required	Y4 🛛 6	43 🛛 A4
٠	Designed to Comply With JEDEC 168-Pin		42 V <sub>CC</sub>
	and 200-Pin SDRAM Buffered DIMM	Y5 4 8	41 A5
	Specification	Y6 🛛 9	
٠	ESD Protection Exceeds 2000 V Per		
	MIL-STD-883, Method 3015; Exceeds 200 V	Y7 11	
	Using Machine Model (C = 200 pF, R = 0)	Y8 12	
٠	Latch-Up Performance Exceeds 250 mA Per	Y9 13 Y10 14	E
	JESD 17	GND 15	
٠	Package Options Include Plastic Shrink	Y11 16	
	Small-Outline (DL), Thin Shrink	Y12 17	
	Small-Outline (DGG), and Thin Very	V <sub>CC</sub> [ 18	
	Small-Outline (DGV) Packages	Y13 19	
desr	cription	Y14 🛛 20	
4030		GND 🛛 21	
	This 16-bit universal bus driver is designed for	Y15 🛛 22	
	1.65-V to 3.6-V V <sub>CC</sub> operation.	Y16 🛛 23	26 A16

1.65-V to 3.6-V  $V_{CC}$  operation. Data flow from A to Y is controlled by the

output-enable  $(\overline{OE})$  input. The device operates in the transparent mode when the latch-enable  $(\overline{LE})$ input is low. When  $\overline{LE}$  is high, the A data is latched if the clock (CLK) input is held at a high or low logic level. If  $\overline{LE}$  is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When  $\overline{OE}$  is high, the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 26- $\Omega$  resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC162334 is characterized for operation from -40°C to 85°C.



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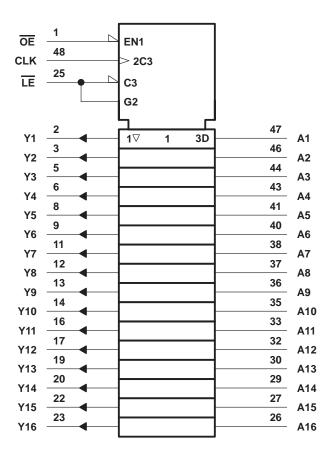
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#### **FUNCTION TABLE**

	INPUTS								
OE	LE	CLK	Α	Y					
Н	Х	Х	Х	Z					
L	L	Х	L	L					
L	L	Х	Н	Н					
L	Н	$\uparrow$	L	L					
L	Н	$\uparrow$	н	н					
L	Н	L or H	Х	Y0 <sup>†</sup>					

<sup>†</sup> Output level before the indicated steady-state input conditions were established

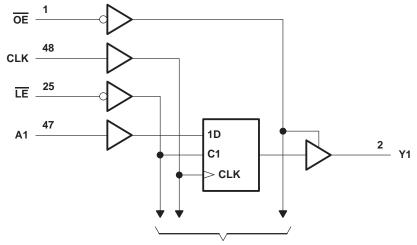
### logic symbol<sup>‡</sup>



<sup>‡</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)



To 15 Other Channels

### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub>	
Input voltage range, VI (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	–0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Continuous output current, I <sub>O</sub>	±50 mA
Continuous current through each V <sub>CC</sub> or GND	±100 mA
	GG package 89°C/W
-	GV package 93°C/W
DL	_ package 94°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



## SN74ALVC162334 **16-BIT UNIVERSAL BUS DRIVER** WITH 3-STATE OUTPUTS SCES127C – FEBRUARY 1998 – REVISED FEBRUARY 1999

### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	3.6	V	
VIH		V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$			
	High-level input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V	
		$V_{CC}$ = 2.7 V to 3.6 V	2			
		V <sub>CC</sub> = 1.65 V to 1.95 V		$0.35 \times V_{CC}$		
VIL	Low-level input voltage	$V_{CC}$ = 2.3 V to 2.7 V		0.7	V	
		$V_{CC}$ = 2.7 V to 3.6 V		0.8		
VI	Input voltage		0	VCC	V	
Vo	Output voltage		0	VCC	V	
		V <sub>CC</sub> = 1.65 V		-2		
1	High-level output current	V <sub>CC</sub> = 2.3 V		-6	<b>–</b>	
ЮН		$V_{CC} = 2.7 V$		-8	mA	
		V <sub>CC</sub> = 3 V		-12		
		V <sub>CC</sub> = 1.65 V		2		
1		$V_{CC} = 2.3 V$	6 8		mA	
IOL	Low-level output current	$V_{CC} = 2.7 V$				
		V <sub>CC</sub> = 3 V		12	]	
$\Delta t / \Delta v$	Input transition rise or fall rate			10	ns/V	
T <sub>A</sub>	Operating free-air temperature	-40	85	°C		

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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PA	RAMETER	TEST CONDITIONS	Vcc	MIN	TYP†	MAX	UNIT	
		I <sub>OH</sub> = -100 μA	1.65 V to 3.6 V	V <sub>CC</sub> -0.2	2			
		$I_{OH} = -2 \text{ mA}$	1.65 V	1.2				
		$I_{OH} = -4 \text{ mA}$	2.3 V	1.9				
Vон			2.3 V	1.7			V	
		I <sub>OH</sub> = -6 mA	3 V	2.4				
		$I_{OH} = -8 \text{ mA}$	2.7 V	2				
		$I_{OH} = -12 \text{ mA}$	3 V	2				
		I <sub>OL</sub> = 100 μA	1.65 V to 3.6 V			0.2		
Vol		I <sub>OL</sub> = 2 mA	1.65 V			0.45		
		I <sub>OL</sub> = 4 mA	2.3 V			0.4		
			2.3 V			0.55	V	
		I <sub>OL</sub> = 6 mA	3 V			0.55		
		I <sub>OL</sub> = 8 mA	2.7 V			0.6		
		I <sub>OL</sub> = 12 mA	3 V			0.8		
lj		$V_I = V_{CC}$ or GND	3.6 V			±5	μΑ	
IOZ		$V_{O} = V_{CC}$ or GND	3.6 V			±10	μΑ	
ICC		$V_{I} = V_{CC} \text{ or } GND, \qquad I_{O} = 0$	3.6 V			40	μΑ	
∆ICC		One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND	3 V to 3.6 V			750	μΑ	
<u></u>	Control inputs		2.2.1/		5		~ <b>F</b>	
Ci	Data inputs	VI = V <sub>CC</sub> or GND	3.3 V		5.5	pF		
Co	Outputs	$V_{O} = V_{CC}$ or GND	3.3 V		7.5		pF	

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> =  $25^{\circ}$ C.

# timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

				V <sub>CC</sub> = 1.8 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT	
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
fclock	Clock frequency	_			‡		150		150		150	MHz	
	Dulas duration	LE low		‡		3.3		3.3		3.3			
tw	Pulse duration	CLK high or low		‡		3.3		3.3		3.3		ns	
	Setup time	Data before CLK↑		‡		1.4		1.7		1.5			
t <sub>su</sub>		Setup time		CLK high	‡		1.2		1.6		1.3		ns
			Data before LE↑	CLK low	‡		1.4		1.5		1.2		
		Data after CLK↑		‡		0.9		0.9		0.9			
th	Hold time	Data after LE↑	CLK high or low	‡		1.1		1.1		1.1		ns	

<sup>‡</sup> This information was not available at the time of publication.



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# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> =	1.8 V	V <sub>CC</sub> = ± 0.2	2.5 V 2 V	V <sub>CC</sub> =	2.7 V	= V <sub>CC</sub> ± 0.3	3.3 V 3 V	UNIT
		(001-01)	MIN T	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
fmax			†		150		150		150		MHz
	A			†	1	4.4		4.5	1.1	3.9	
<sup>t</sup> pd	LE	Y		†	1	5.8		6	1.3	5	ns
	CLK			†	1	5.2		5.4	1	4.9	
ten	OE	Y		†	1	6.4		6.4	1.1	5.4	ns
<sup>t</sup> dis	OE	Y		†	1	4.7		5.1	1.7	5	ns

<sup>†</sup> This information was not available at the time of publication.

### switching characteristics from $0^{\circ}$ C to $65^{\circ}$ C, C<sub>L</sub> = 50 pF

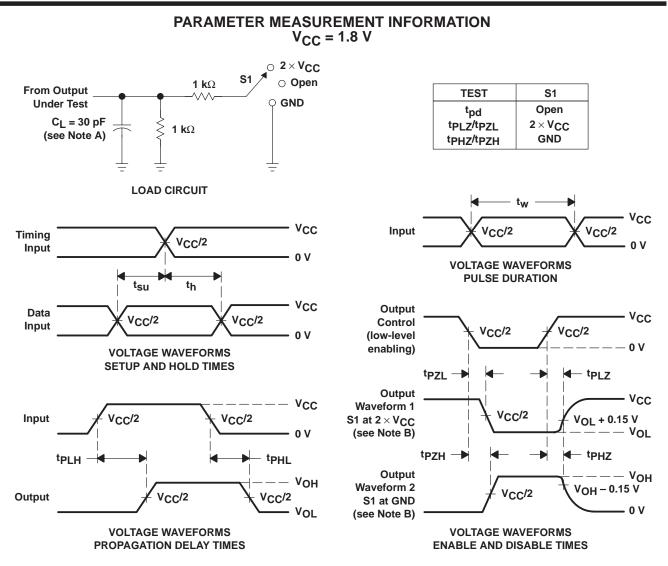
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1	UNIT	
		(661161)	MIN	MAX	
<sup>t</sup> pd	A	Y	1.2	3.8	20
	CLK	Y	1.1	4.8	ns

## operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8 V TYP	V <sub>CC</sub> = 2.5 V V <sub>CC</sub> = 3.3 V TYP TYP		UNIT	
	Power dissipation capacitance	Outputs enabled		†	31	36	ρF
C <sub>pd</sub>		Outputs disabled	$C_{L} = 0$ , $f = 10 \text{ MHz}$	†	7	11	рг

<sup>†</sup> This information was not available at the time of publication.



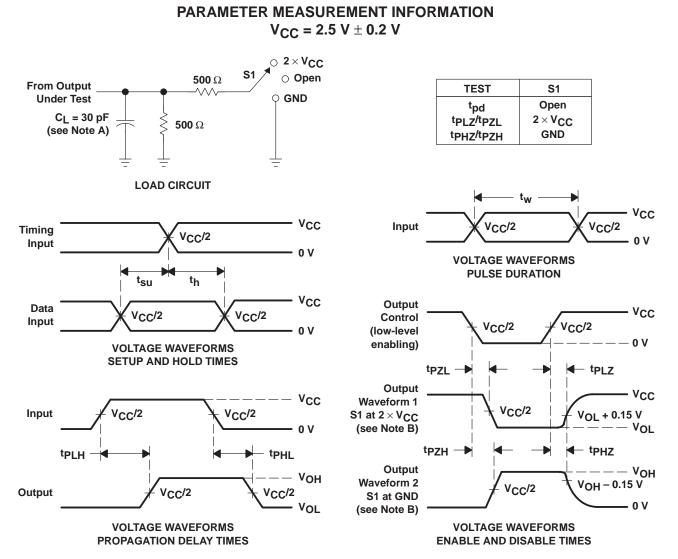


- NOTES: A. CL includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2 ns, t<sub>f</sub>  $\leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G. tPLH and tPHL are the same as tpd.

#### Figure 1. Load Circuit and Voltage Waveforms



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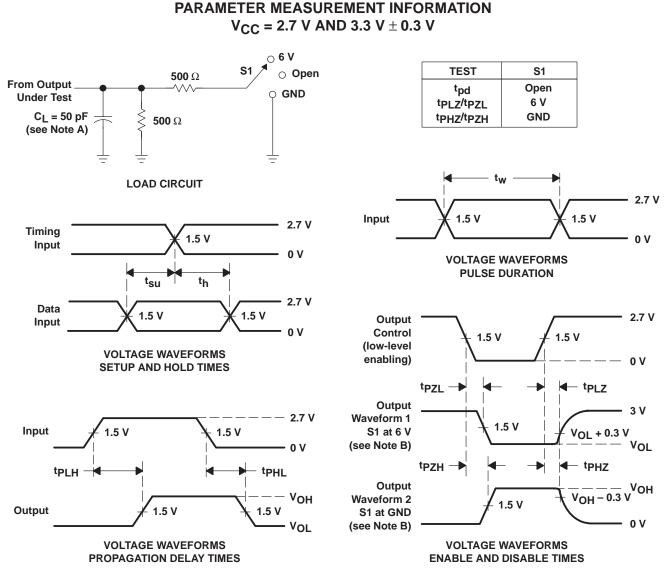


- NOTES: A. CL includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control. C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2 ns, t<sub>f</sub>  $\leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.

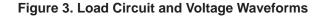
  - E. tPLZ and tPHZ are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tPLH and tPHL are the same as tpd.

### Figure 2. Load Circuit and Voltage Waveforms





- NOTES: A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLZ and tpHZ are the same as tdis.
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .





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